

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
50V	2.0Ω @ $V_{GS} = 5.0V$	300 mA
	2.5Ω @ $V_{GS} = 2.5V$	200 mA

Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage (1.0V max)
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

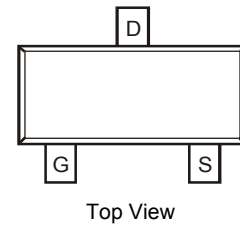
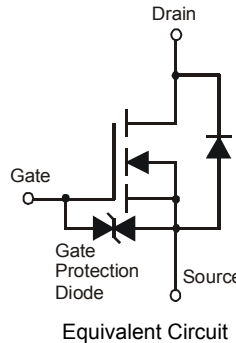
Description and Applications

This new generation 50V N-Channel Enhancement Mode MOSFET has been designed to minimize RDS(on) and yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and Load switch.

- Load switches
- Level switches

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

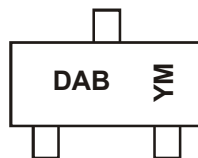


Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMN5L06K-7	Commercial	SOT23	3000/Tape & Reel
DMN5L06KQ-7	Automotive	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DAB = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: T = 2006)
 M = Month (ex: 9 = September)

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	T	U	V	W	X	Y	Z	A	B	C	D	E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current (Note 5)	I_D	Continuous	300
		Pulsed (Note 6)	800

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	350	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	—	—	V	$V_{GS} = 0V, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	60	nA	@ $T_C = +25^\circ\text{C}$ $V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	—	—	1	μA	$V_{GS} = \pm 12V, V_{DS} = 0V$
				500	nA	$V_{GS} = \pm 10V, V_{DS} = 0V$
				50	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.49	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	3.0	Ω	$V_{GS} = 1.8V, I_D = 50\text{mA}$
				2.5		$V_{GS} = 2.5V, I_D = 50\text{mA}$
				2.0		$V_{GS} = 5.0V, I_D = 50\text{mA}$
On-State Drain Current	$I_{D(on)}$	0.5	1.4	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	$ Y_{fs} $	200	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage	V_{SD}	0.5	—	1.4	V	$V_{GS} = 0V, I_S = 115\text{mA}$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	5.0	pF	

- Notes:
5. Device mounted on FR-4 PCB
 6. Pulse width $\leq 10\text{ms}$, Duty Cycle $\leq 1\%$.
 7. Short duration pulse test used to minimize self-heating effect.

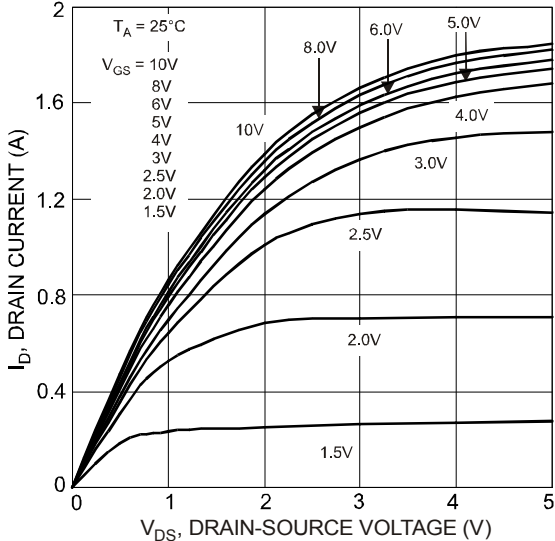


Fig. 1 Typical Output Characteristics

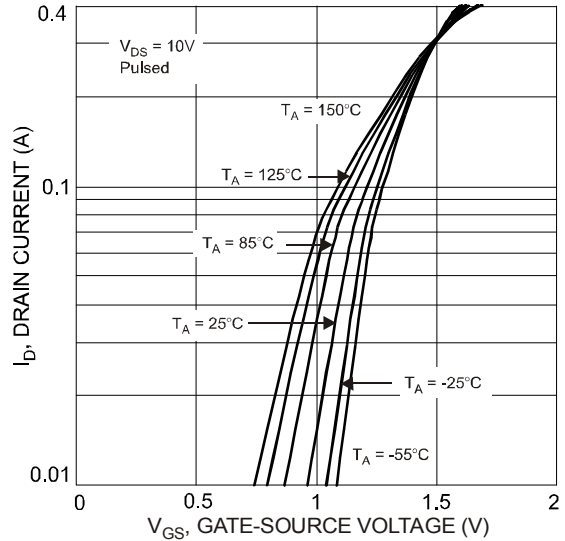


Fig. 2 Typical Transfer Characteristics

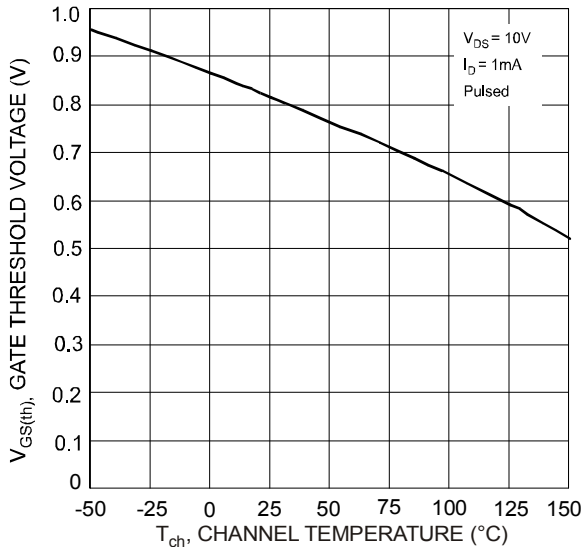


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

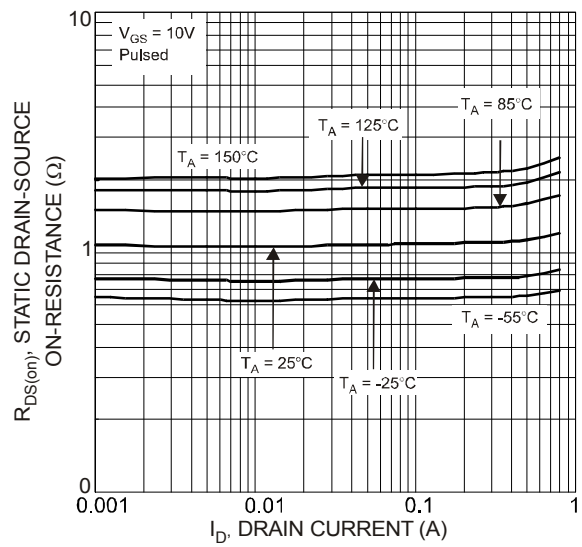


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

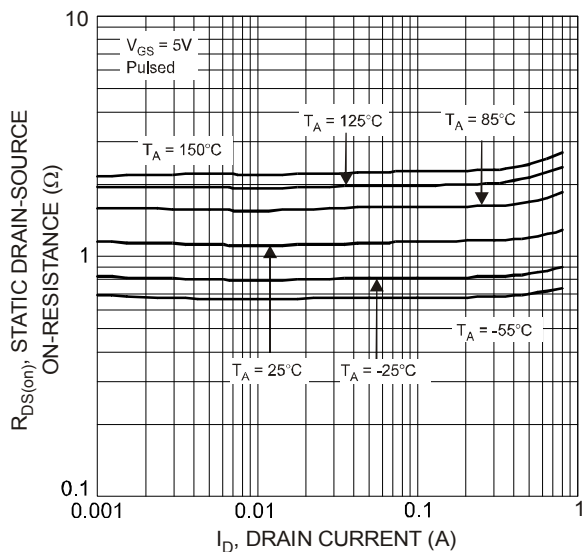


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

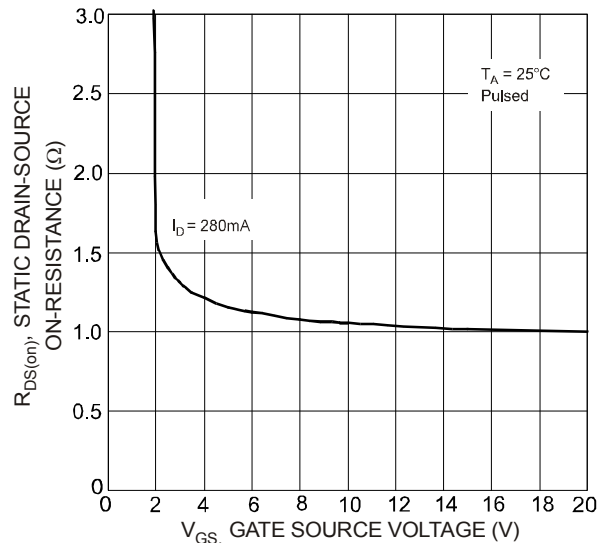


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

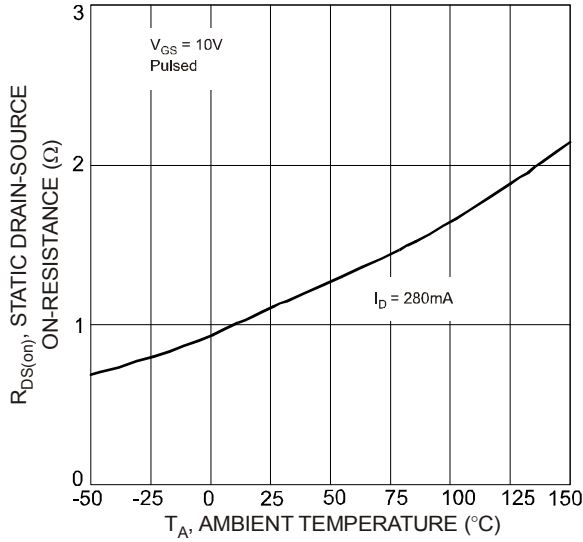


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

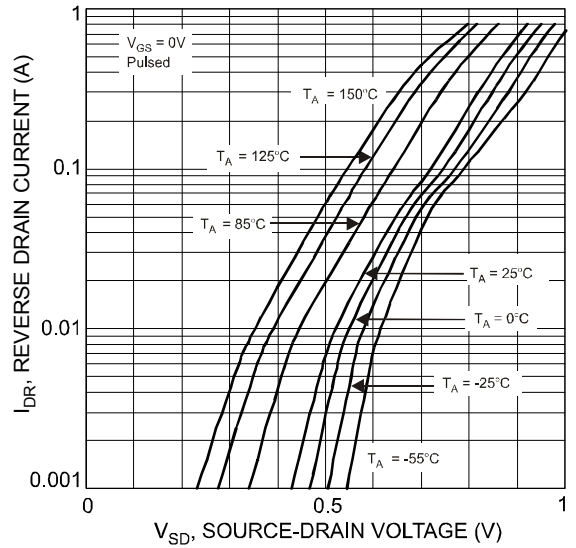


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

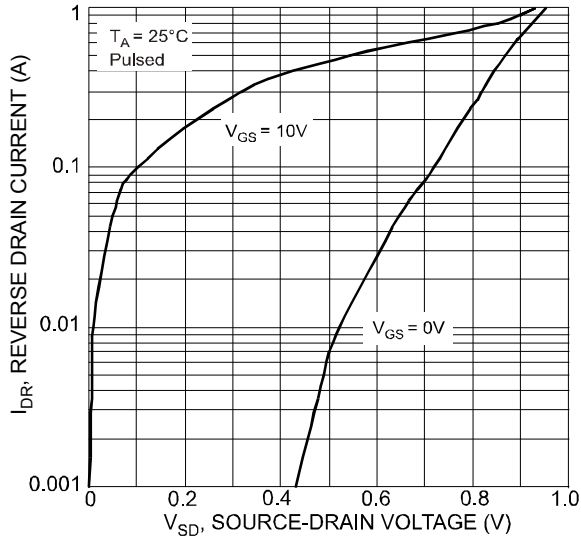


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

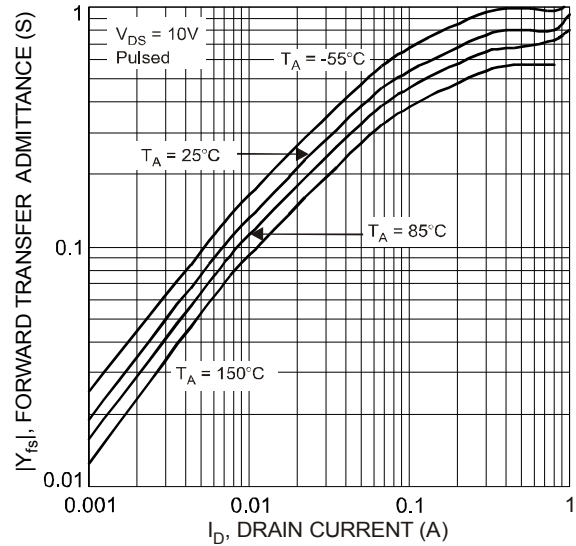


Fig. 10 Forward Transfer Admittance vs. Drain Current

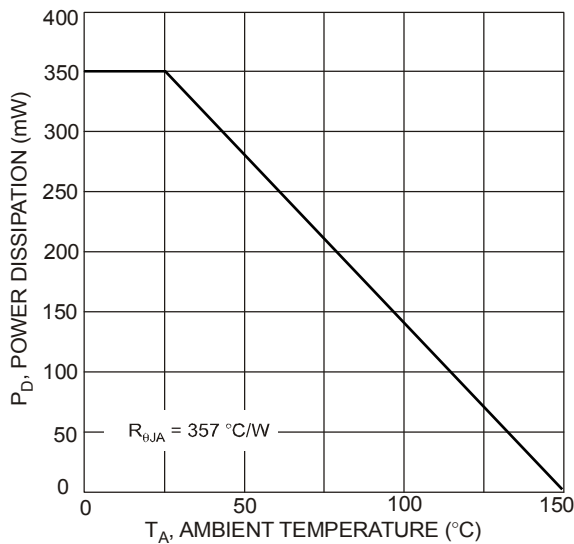


Fig. 11 Derating Curve - Total

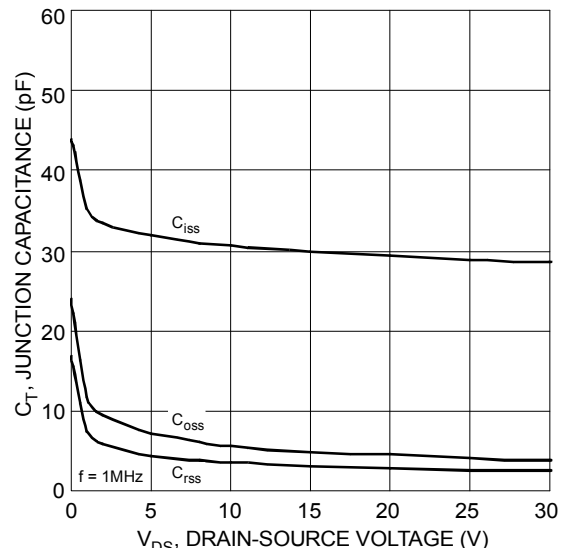
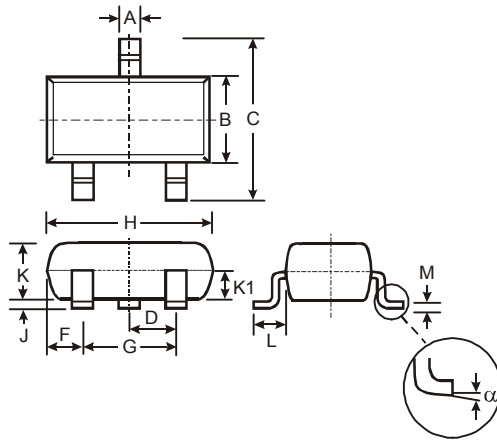


Figure 12 Typical Junction Capacitance

Package Outline Dimensions

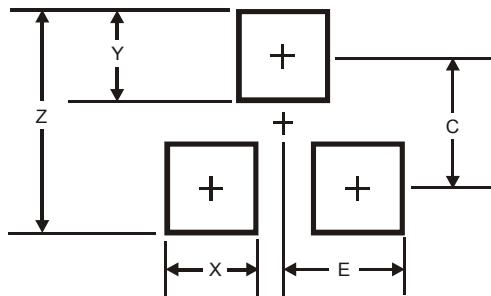
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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